

## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
30	0.0030 at V <sub>GS</sub> = 10 V	30	36
	0.0040 at V <sub>GS</sub> = 4.5 V	27	

### FEATURES

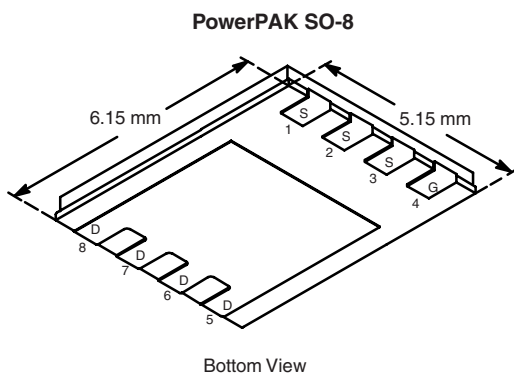
- Halogen-free available
- Ultra-Low On-Resistance Using High Density TrenchFET<sup>®</sup> Gen II Power MOSFET Technology
- Q<sub>g</sub> Optimized
- New Low Thermal Resistance PowerPAK<sup>®</sup> Package with Low 1.07 mm Profile
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested



**RoHS**  
COMPLIANT

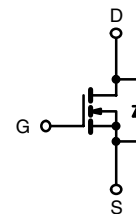
### APPLICATIONS

- Low-Side DC/DC Conversion
  - Notebook
  - Server
  - Workstation



Bottom View

Ordering Information: Si7336ADP-T1-E3 (Lead (Pb)-free)  
Si7336ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	30
		T <sub>A</sub> = 70 °C	25
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	70	A
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	4.5	
Avalanche Current	I <sub>AS</sub>	L = 0.1 mH	50
Maximum Power Dissipation <sup>a</sup>		T <sub>A</sub> = 25 °C	5.4
	T <sub>A</sub> = 70 °C	3.4	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	R <sub>thJA</sub>	18	23	°C/W
	Steady State		50	65	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	1.0	1.5	

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

<b>MOSFET SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
		$V_{DS} = 30\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 25\ \text{A}$		0.0024	0.0030	$\Omega$
		$V_{GS} = 4.5\ \text{V}, I_D = 19\ \text{A}$		0.0031	0.0040	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\ \text{V}, I_D = 25\ \text{A}$		110		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.9\ \text{A}, V_{GS} = 0\ \text{V}$		0.72	1.1	V
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\ \text{V}, V_{GS} = 0\ \text{V}, f = 1\ \text{MHz}$		5600		$\mu\text{F}$
Output Capacitance	$C_{oss}$			860		
Reverse Transfer Capacitance	$C_{rss}$			415		
Total Gate Charge	$Q_g$	$V_{DS} = 15\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 20\ \text{A}$		36	50	$\text{nC}$
Gate-Source Charge	$Q_{gs}$			18		
Gate-Drain Charge	$Q_{gd}$			10		
Gate Resistance	$R_g$		0.6	1.3	2.0	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1.0\ \text{A}, V_{GEN} = 10\ \text{V}, R_G = 6\ \Omega$		24	35	$\text{ns}$
Rise Time	$t_r$			16	25	
Turn-Off Delay Time	$t_{d(off)}$			90	140	
Fall Time	$t_f$			32	50	
Source-Drain Reverse Recovery Time	$t_{rr}$		$I_F = 2.9\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		45	

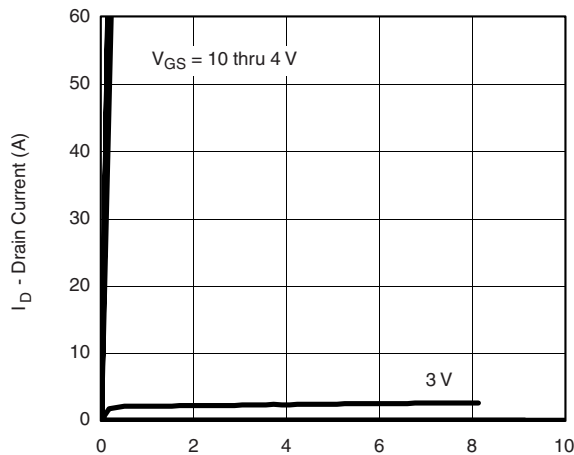
Notes:

a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

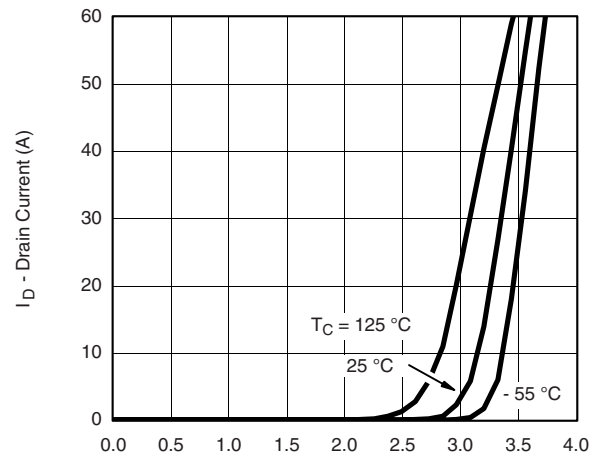
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$ , unless otherwise noted

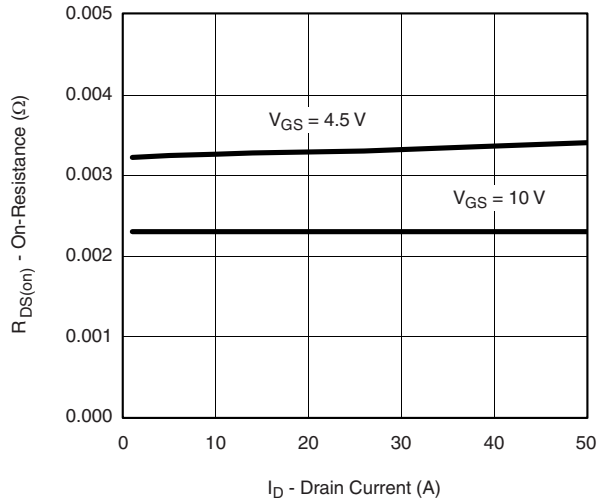


**Output Characteristics**

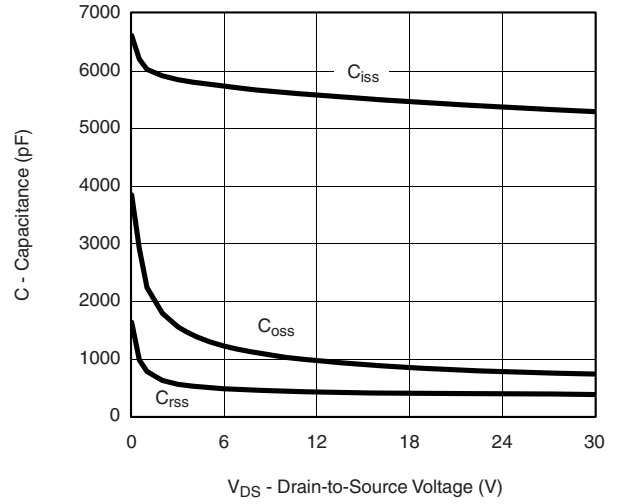


**Transfer Characteristics**

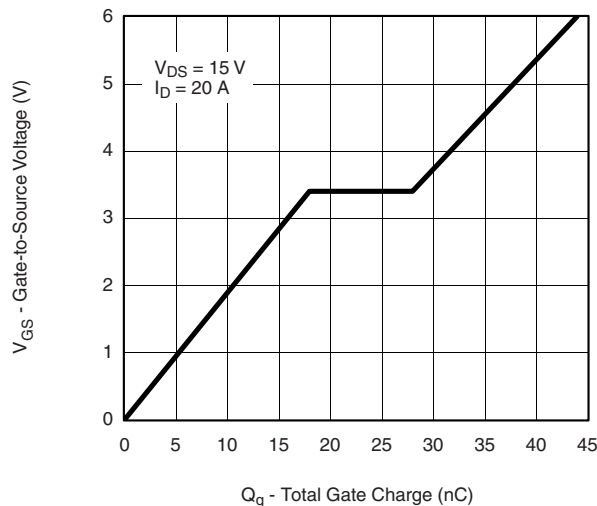
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



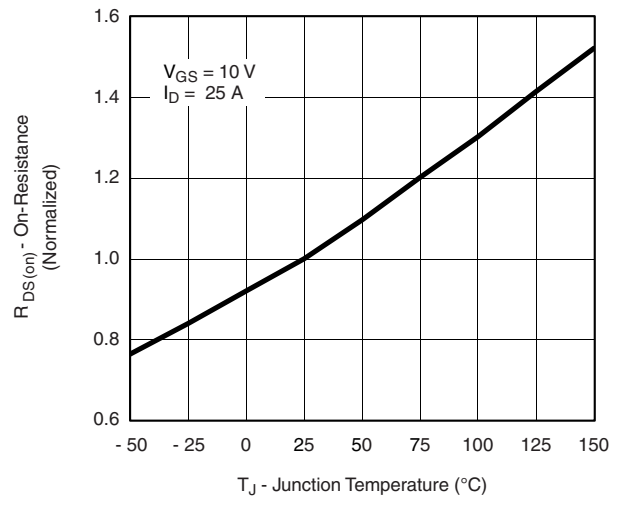
**On-Resistance vs. Drain Current**



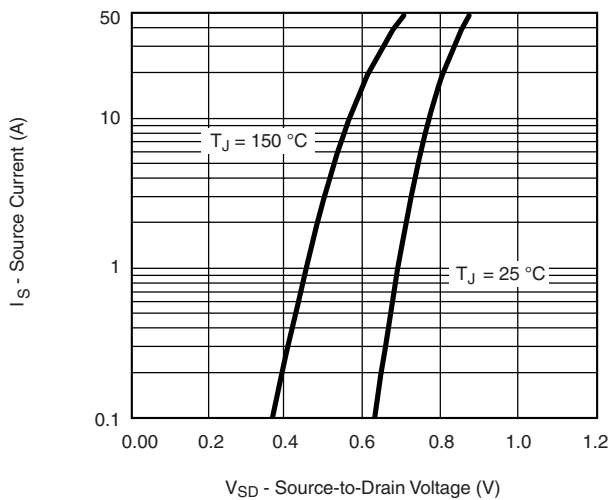
**Capacitance**



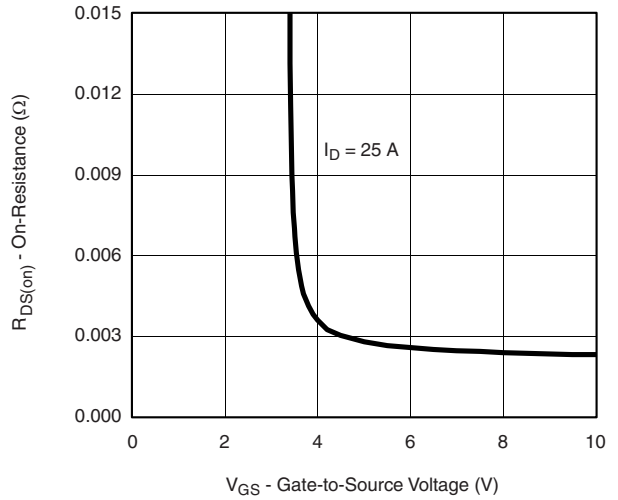
**Gate Charge**



**On-Resistance vs. Junction Temperature**

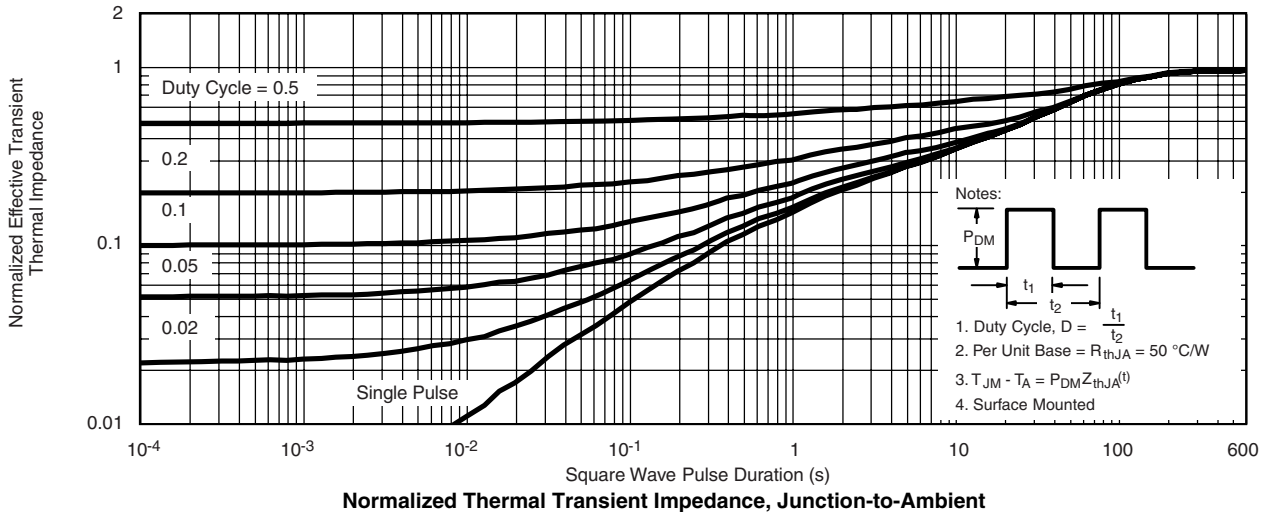
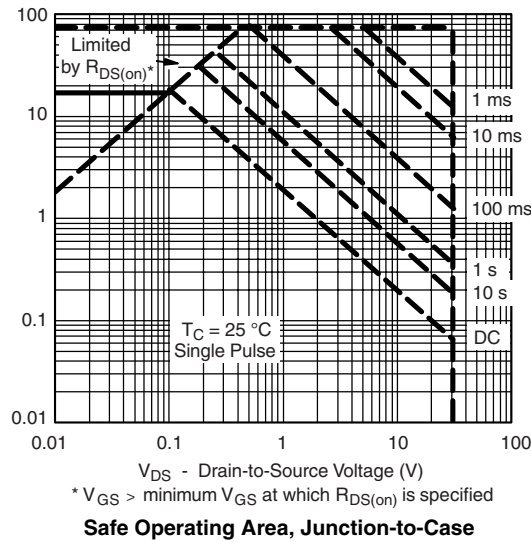
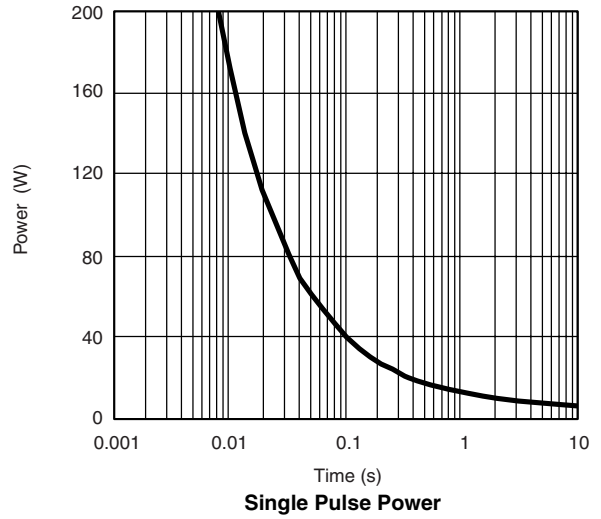
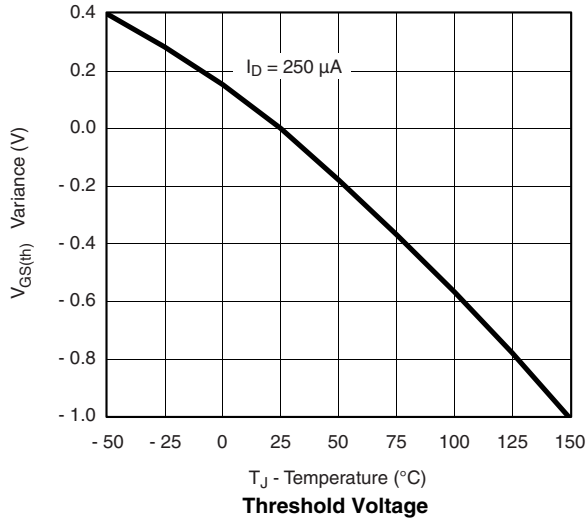


**Source-Drain Diode Forward Voltage**

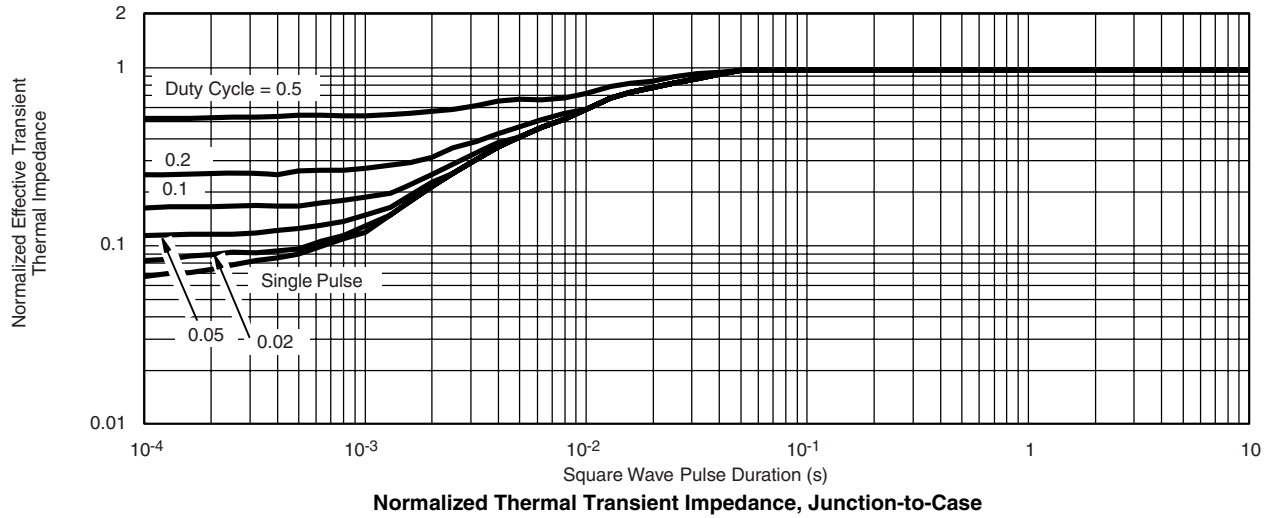


**On-Resistance vs. Gate-to-Source Voltage**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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